

**isc Silicon NPN Power Transistor**

**2SC5265**

**DESCRIPTION**

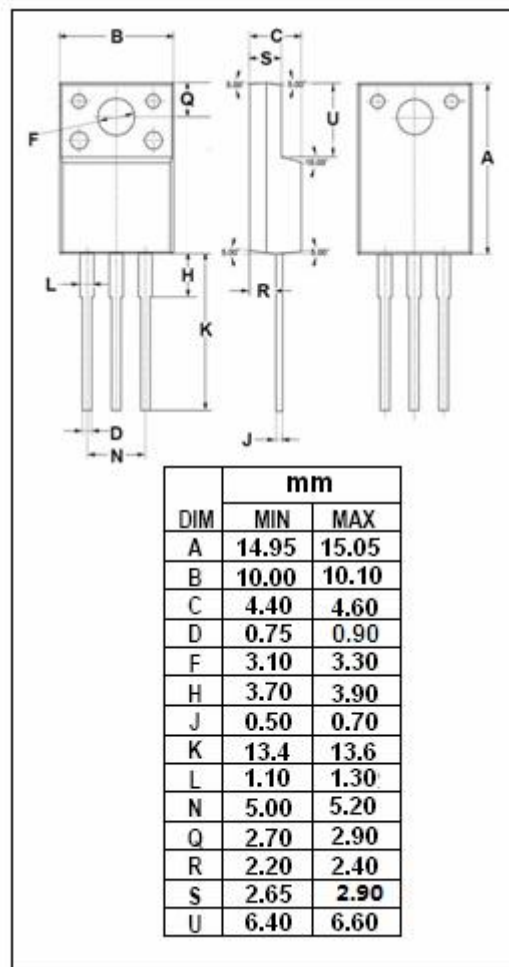
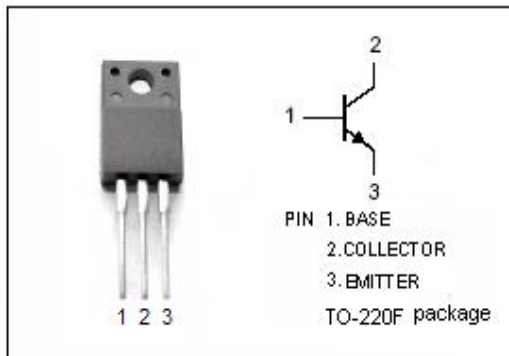
- High Breakdown Voltage-(Vcb=1200V)
- High Reliability
- Adoption of MBIT proces

**APPLICATIONS**

- Inverter-controlled Lighting

**ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	1200	V
V <sub>CEO</sub>	Collector-Emitter Voltage	600	V
V <sub>EBO</sub>	Emitter-Base Voltage	9	V
I <sub>C</sub>	Collector Current- Continuous	4	A
I <sub>CM</sub>	Collector Current-Peak	8	A
P <sub>C</sub>	Collector Power Dissipation @ T <sub>C</sub> =25°C	30	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C



**isc Silicon NPN Power Transistor****2SC5265****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=10\text{mA}$ ; $I_B=0$	600			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2\text{A}$ ; $I_B=0.4\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=2\text{A}$ ; $I_B=0.4\text{A}$			1.5	V
$I_{CES}$	Collector Cutoff Current	$V_{CE}=1200\text{V}$ ; $R_{BE}=0$			1.0	mA
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=600\text{V}$ ; $I_E=0$			10	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=9\text{V}$ ; $I_C=0$			1.0	mA
$h_{FE-1}$	DC Current Gain	$I_C=0.3\text{A}$ ; $V_{CE}=5\text{V}$	30		50	
$h_{FE-2}$	DC Current Gain	$I_C=1.5\text{A}$ ; $V_{CE}=5\text{V}$	10			